

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF466** is Designed for power amplifier applications from 2.0 to 30MHz.

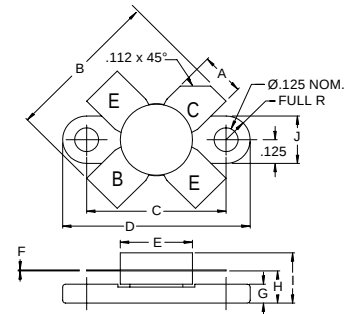
FEATURES:

- $P_G = 15$ dB min. at 40 W/30 MHz
- $IMD_3 = -30$ dBc max. at 40 W (PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	6.0 A
V_{CBO}	65 V
V_{CEO}	35 V
P_{DISS}	175 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	1.0 $^\circ C/W$

PACKAGE STYLE .380 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100$ mA	35			V
BV_{CES}	$I_C = 100$ mA	65			V
BV_{EBO}	$I_E = 1.0$ mA	4.0			V
I_{CES}	$V_E = 28$ V			5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 0.5$ A	10		80	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz		125	200	pF
G_{PE}	$V_{CE} = 28$ V $I_{CQ} = 20$ mA $f = 30$ MHz	15	19		dB
η	$P_{OUT} = 40$ W (PEP)	40			%
IMD_3			-40	-30	dBc